

BSP372-VB Datasheet N-Channel 100-V (D-S) MOSFET

| PRODU | CT SUMMARY | |
|---------------------|----------------------------------|--------------------|
| V _{DS} (V) | $R_{DS(on)}(\Omega)$ | I _D (A) |
| 100 | 0.100 at $V_{GS} = 10 \text{ V}$ | 5.0 |
| 100 | 0.120 at V _{GS} = 4.5 V | 4.5 |

FEATURES

 Halogen-free According to IEC 61249-2-21 Definition

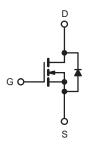


- 175 °C Maximum Junction Temperature
- Compliant to RoHS Directive 2002/95/EC









| N-Channel | MOSEET |
|-----------|--------|

| ABSOLUTE MAXIMUM RATINGS | T _A = 25 °C, unles | ss otherwise r | noted | | |
|--|-------------------------------|-----------------------------------|----------------------|--------------|------|
| Parameter | | Symbol | 10 s | Steady State | Unit |
| Drain-Source Voltage | | V _{DS} | 100 | | V |
| Gate-Source Voltage | | V_{GS} | V _{GS} ± 20 | | V |
| Continuous Drain Current (T _{.1} = 175 °C) ^a | T _A = 25 °C | l _n | 5.0 | 4.5 | A |
| Continuous Diain Current (1) = 175 C) | T _A = 70 °C | ΙD | 3.5 | 3.0 | |
| Pulsed Drain Current | | I _{DM} | 25 | | A |
| Avalanche Current | | I _{AS} | 15 | | |
| Single Pulse Avalanche Energy | | E _{AS} | 11 | | mJ |
| Manianum Danum Disainationa | T _A = 25 °C | P _D | 3.3 | 1.7 | W |
| Maximum Power Dissipation ^a | T _A = 70 °C | • В | 2.3 | 1.2 | VV |
| Operating Junction and Storage Temperature Ran | ige . | T _J , T _{stg} | - 55 | to 175 | °C |

| THERMAL RESISTANCE RATINGS | | | | | |
|--|--------------|-------------------|---------|---------|------|
| Parameter | | Symbol | Typical | Maximum | Unit |
| Mariana lanation to Ambient 3 | t ≤ 10 s | R _{thJA} | 36 | 45 | |
| Maximum Junction-to-Ambient ^a | Steady State | | 75 | 90 | °C/W |
| Maximum Junction-to-Foot (Drain) | Steady State | R_{thJF} | 17 | 20 | |

Notes:

a. Surface Mounted on 1" x 1" FR4 board.



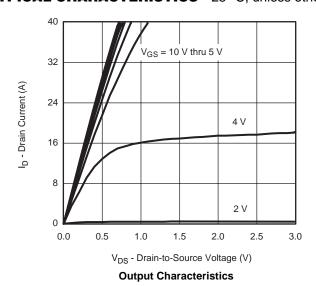
| Parameter | Symbol | Test Conditions | Min. | Тур. | Max. | Unit | |
|---|---------------------|---|------|-------|-------|--------|--|
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ | 100 | | | V | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | 1.5 | | 3 | V | |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ± 100 | nA | |
| Zoro Coto Voltago Proin Current | 1 | V _{DS} = 100 V, V _{GS} = 0 V | | | 1 | Δ | |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$ | | | 20 μΑ | | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$ | 40 | | | Α | |
| | | $V_{GS} = 10 \text{ V}, I_D = 6.0 \text{ A}$ | | 0.110 | | | |
| | | $V_{GS} = 10 \text{ V}, I_D = 4.0 \text{ A}, T_J = 125 \text{ °C}$ | | 0.122 | | | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | $V_{GS} = 10 \text{ V}, I_D = 4.0 \text{ A}, T_J = 175 ^{\circ}\text{C}$ | | 0.140 | | Ω S | |
| | | $V_{GS} = 4.5 \text{ V}, I_D = 3.1 \text{ A}$ | | 0.120 | | | |
| Forward Transconductance ^a | 9 _{fs} | $V_{DS} = 15 \text{ V}, I_D = 4.0 \text{ A}$ | | 25 | | S | |
| Diode Forward Voltage ^a | V_{SD} | I _S = 1.7 A, V _{GS} = 0 V | | 0.8 | 1.2 | V | |
| Dynamic ^b | | | | | | | |
| Total Gate Charge | Q_g | | | 18 | 27 | | |
| Gate-Source Charge | Q_{gs} | $V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 4.0 \text{ A}$ | | 3.4 | | nC | |
| Gate-Drain Charge | Q_{gd} | | | 5.3 | | | |
| Gate Resistance | R_g | $V_{GS} = 0.1 \text{ V, f} = 5 \text{ MHz}$ | 0.5 | 1.4 | 2.4 | Ω | |
| Turn-On Delay Time | t _{d(on)} | | | 10 | 20 | | |
| Rise Time | t _r | V_{DD} = 50 V, R_L = 30 Ω | | 10 | 20 | | |
| Turn-Off Delay Time | t _{d(off)} | $I_D\cong 1$ A, $V_{GEN}=10$ V, $R_g=6$ Ω | | 25 | 50 | ns | |
| Fall Time | t _f | | | 12 | 24 | | |
| Source-Drain Reverse Recovery Time | t _{rr} | $I_F = 1.7 \text{ A}, dI/dt = 100 \text{ A/}\mu\text{s}$ | | 50 | 80 | | |

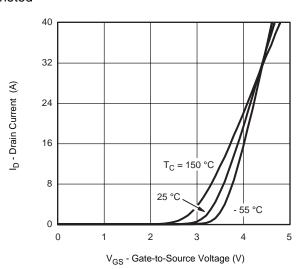
Notes:

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

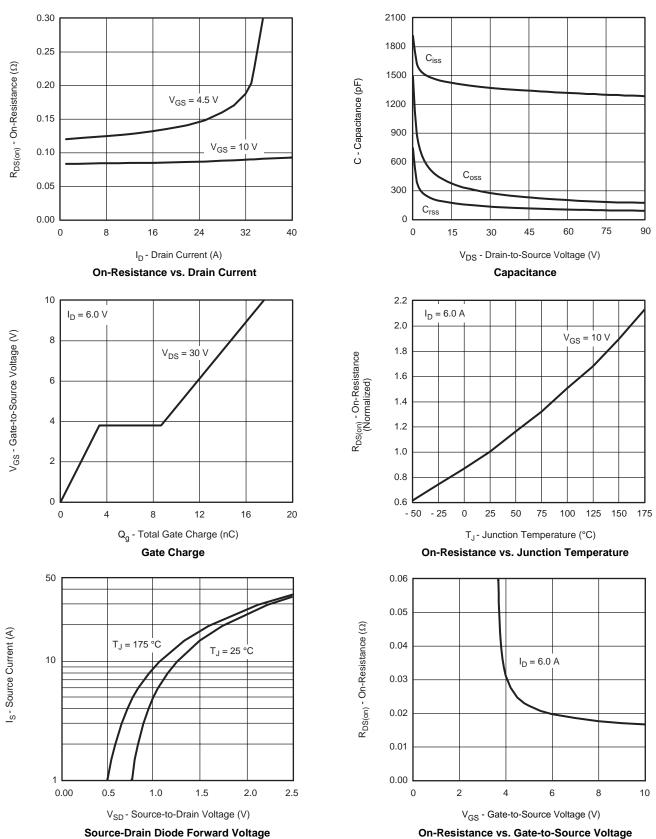




Transfer Characteristics

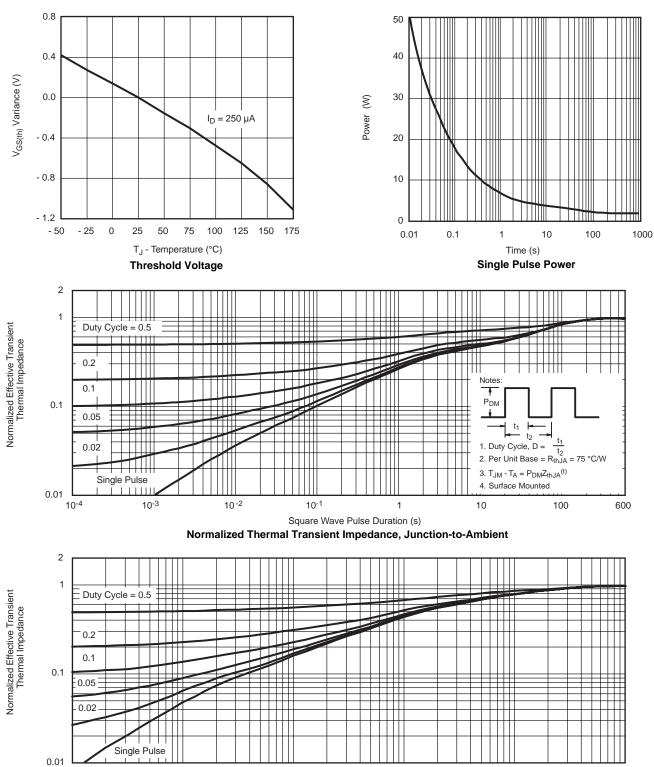


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





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Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Foot

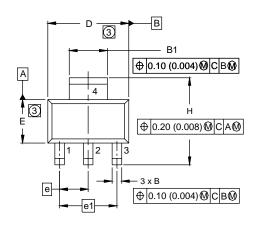
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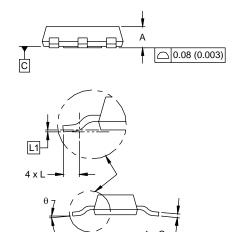
10-4

10-3



SOT-223 (HIGH VOLTAGE)





| DIM. | MILLIMETERS | | INCHES | |
|------|-------------|------|------------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| Α | 1.55 | 1.80 | 0.061 | 0.071 |
| В | 0.65 | 0.85 | 0.026 | 0.033 |
| B1 | 2.95 | 3.15 | 0.116 | 0.124 |
| С | 0.25 | 0.35 | 0.010 | 0.014 |
| D | 6.30 | 6.70 | 0.248 | 0.264 |
| E | 3.30 | 3.70 | 0.130 | 0.146 |
| е | 2.30 BSC | | 0.0905 BSC | |
| e1 | 4.60 BSC | | 0.181 | BSC |
| Н | 6.71 | 7.29 | 0.264 | 0.287 |
| L | 0.91 | - | 0.036 | - |
| L1 | 0.061 BSC | | 0.0024 | 4 BSC |
| θ | - | 10' | - | 10' |

ECN: S-82109-Rev. A, 15-Sep-08

DWG: 5969

Notes

- 1. Dimensioning and tolerancing per ASME Y14.5M-1994.
- 2. Dimensions are shown in millimeters (inches).
- 3. Dimension do not include mold flash.
- 4. Outline conforms to JEDEC outline TO-261AA.



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